



#### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
-20V	$16m\Omega$ @ $V_{GS} = -4.5V$	-9.0A
-20V	22mΩ @ V <sub>GS</sub> = -2.5V	-7.7A

### **Description and Applications**

This MOSFET is designed to minimize on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for highefficiency power management applications.

- **Battery Management Application**
- **Power Management Functions**
- **DC-DC Converters**

### **Features and Benefits**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

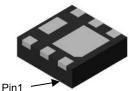
#### Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202. Method 208 @4
- Weight: 0.007 grams (Approximate)

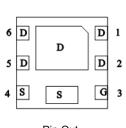




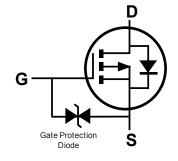




Top View **Bottom View** 







**Equivalent Circuit** 

### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP2021UFDF-7	U-DFN2020-6	3000/Tape & Reel
DMP2021UFDF-13	U-DFN2020-6	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



# **Marking Information**

Site 1

U-DFN2020-6



P1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Ī	Year	2014	2015	 2020	2021	2022	2023
	Code	В	С	 Н	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2



P1 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Date Code Ite								
Year	2019	2020	2021	2022	2023	2024	2025	2026
Code	9	0	1	2	3	4	5	6

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Υ	Z



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			$V_{DSS}$	-20	V
Gate-Source Voltage			$V_{GSS}$	±8	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	l <sub>D</sub>	-9.0 -7.2	А	
Continuous Diain Current (Note 6) VGS = -4.5V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-11.1 -8.9	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			$I_{DM}$	-60	Α
Continuous Source-Drain Diode Current (Note 6)	Is	-2.4	Α		
Avalanche Current (Note 7) L = 0.1mH	las	-27	Α		
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	38	mJ

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissination (Note 5)	T <sub>A</sub> = +25°C	В	0.73	W	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	$P_{D}$	0.47	VV	
Thermal Peciatones, Junction to Ambient (Note 5)	Steady State	- Г	172	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	121	C/VV	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	D-	2.02	W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	$P_{D}$	1.30	٧٧	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	- Г	63		
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	42	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{ heta JC}$	18		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					•	
Drain-Source Breakdown Voltage	$BV_{DSS}$	-20		_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.35	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			12	16		$V_{GS} = -4.5V$ , $I_D = -7.0A$
Static Drain-Source On-Resistance	Dec (a)	_	15	22	mΩ	$V_{GS} = -2.5V$ , $I_D = -5.0A$
Static Diain-Source On-Resistance	R <sub>DS</sub> (ON)		19	40	11122	$V_{GS} = -1.8V$ , $I_D = -3.0A$
			21	80		$V_{GS} = -1.5V, I_D = -1.0A$
Diode Forward Voltage	$V_{SD}$	_	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C <sub>iss</sub>	1	2,760	_		V 45V V 0V
Output Capacitance	Coss	-	262	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	220	_		1 = 1.01/11/12
Gate Resistance	$R_g$	_	16	30	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	34	_		
Total Gate Charge (V <sub>GS</sub> = -8V)	Qg	_	59	_	nC	151/ 1 404
Gate-Source Charge	Q <sub>gs</sub>	_	3.5	_	IIC	$V_{DS} = -15V, I_{D} = -4.0A$
Gate-Drain Charge	Q <sub>gd</sub>	_	8.3	_		
Turn-On Delay Time	t <sub>D(on)</sub>	_	7.5	_		
Turn-On Rise Time	t <sub>r</sub>	_	25	_		$V_{DS} = -15V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t <sub>D(off)</sub>	_	125	_	ns	$R_G = 1\Omega, I_D = -4.0A$
Turn-Off Fall Time	t <sub>f</sub>	_	96	_	1	
Reverse Recovery Time	t <sub>rr</sub>	_	48	_	ns	I <sub>F</sub> = -1.0A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>rr</sub>	_	33	_	nC	I <sub>F</sub> = -1.0A, di/dt = 100A/µs

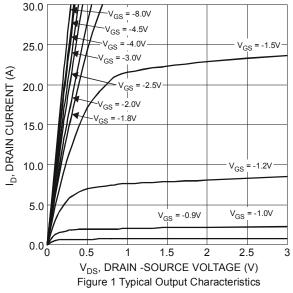
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. Notes:

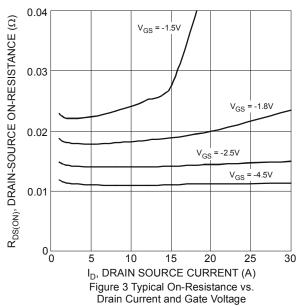
8. Short duration pulse test used to minimize self-heating effect.

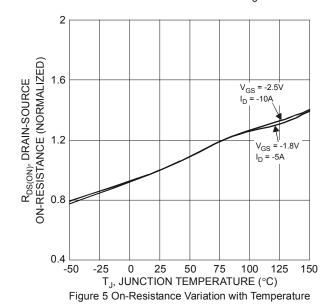
9. Guaranteed by design. Not subject to product testing.

<sup>7.</sup>  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J$  = +25°C.

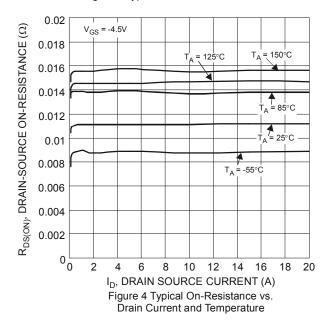








20 V<sub>DS</sub> = -5.0V 18 16 ID, DRAIN CURRENT (A) 14 12 10 8 6 4  $T_A =$ 2 0 0 1.5 2.5  $V_{GS}$ , GATE-SOURCE VOLTAGE (V) Figure 2 Typical Transfer Characteristics



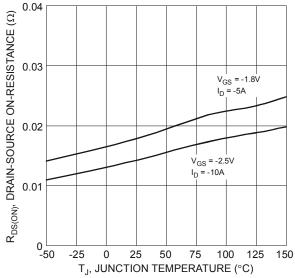


Figure 6 On-Resistance Variation with Temperature



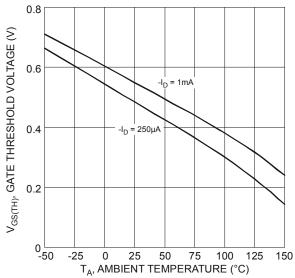
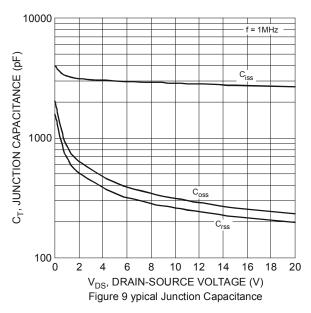
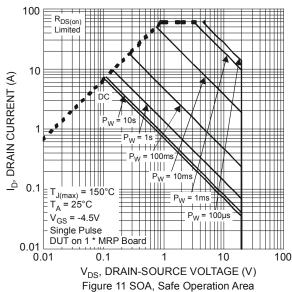
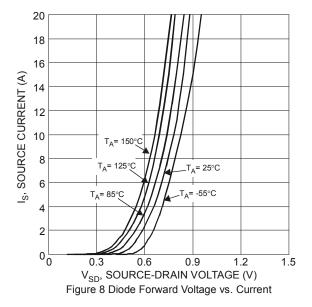
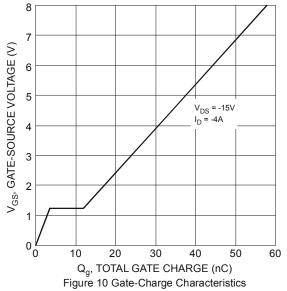


Figure 7 Gate Threshold Variation vs. Ambient Temperature

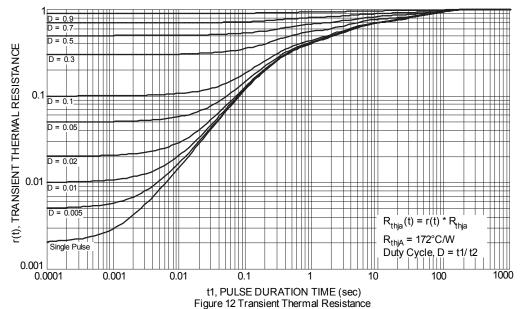










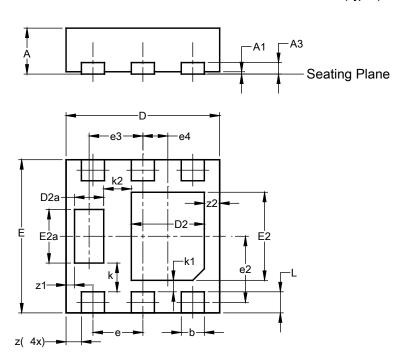




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)

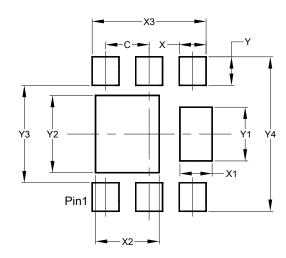


	U-DFN2020-6								
	(Type F)								
Dim	Min	Max	Тур						
Α	0.57	0.57 0.63 0.60							
A1	0.00	0.05	0.03						
A3	ı	-	0.15						
b	0.25	0.35	0.30						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
D2a	0.33	0.43	0.38						
Е	1.95 2.05 2.00								
E2	1.05 1.25 1.15								
E2a	0.65	0.75	0.70						
е		0.65 BS	С						
e2	C	).863 BS	SC						
е3		0.70 BS	С						
e4	C	).325 BS	SC						
k		0.37 BS							
k1		0.15 BS	С						
k2		0.36 BS	С						
L	0.225 0.325 0.275								
Z	0.20 BSC								
z1	0.110 BSC								
z2		0.20 BS	С						
All D	imens	ions in	mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)



Dimensions	Value
פווטופווסוטווס	(in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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